

Low Vcesat NPN Epitaxial Planar Transistor

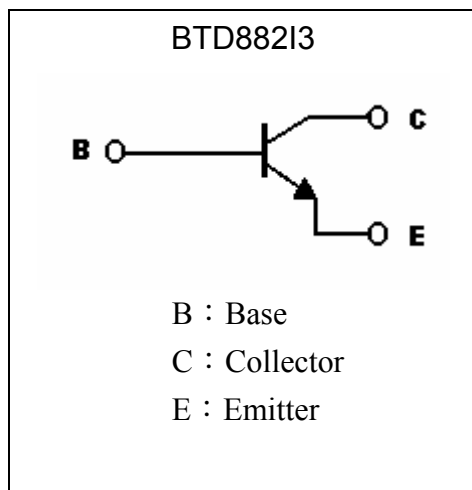
BTD882I3

BV_{CEO}	30V
I_C	3A
R_{CESAT}	125m Ω typ.

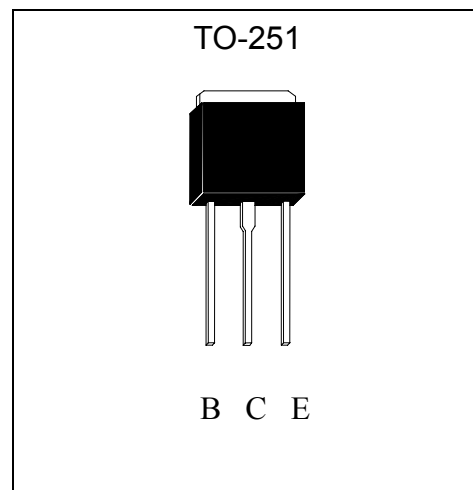
Features

- Low $V_{CE(sat)}$, typically 0.25V at $I_C / I_B = 2A / 0.2A$
- Excellent current gain characteristics
- Complementary to BTB772I3
- RoHS compliant package

Symbol



Outline



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	$I_C(DC)$	3	A
	$I_C(Pulse)$	7 *1	A
Power Dissipation	$P_d(T_a=25^\circ C)$	1	W
	$P_d(T_c=25^\circ C)$	10	
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Note : *1. Single Pulse $P_w \leq 350\mu s, Duty \leq 2\%$.

**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	40	-	-	V	I _C =50μA, I _E =0
BV _{CE0}	30	-	-	V	I _C =1mA, I _B =0
BV _{EB0}	5	-	-	V	I _E =50μA, I _C =0
I _{CB0}	-	-	1	μA	V _{CB} =30V, I _E =0
I _{EB0}	-	-	1	μA	V _{EB} =3V, I _C =0
*V _{CE(sat)}	-	0.25	0.5	V	I _C =2A, I _B =0.2A
*V _{BE(sat)}	-	-	2	V	I _C =2A, I _B =0.2A
*h _{FE1}	150	-	-	-	V _{CE} =2V, I _C =20mA
*h _{FE2}	180	-	560	-	V _{CE} =2V, I _C =1A
f _T	-	90	-	MHz	V _{CE} =5V, I _C =0.1A, f=100MHz
Cob	-	45	-	pF	V _{CB} =10V, f=1MHz

*Pulse Test : Pulse Width ≤380μs, Duty Cycle ≤2%

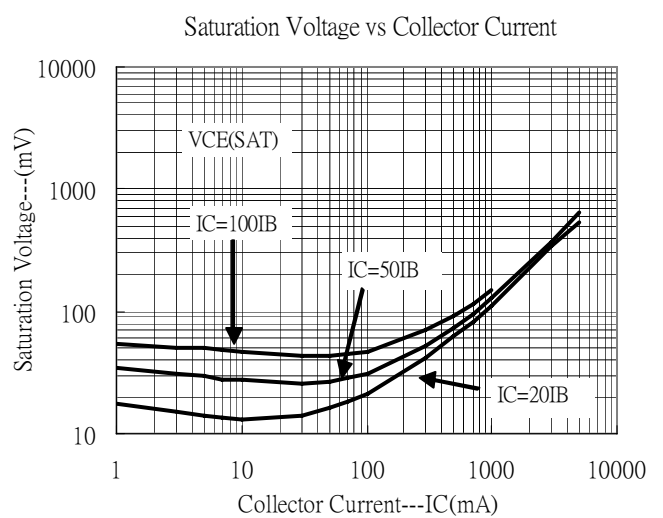
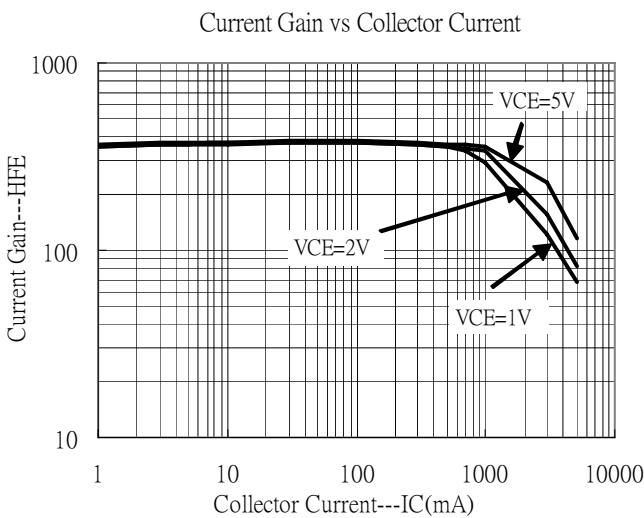
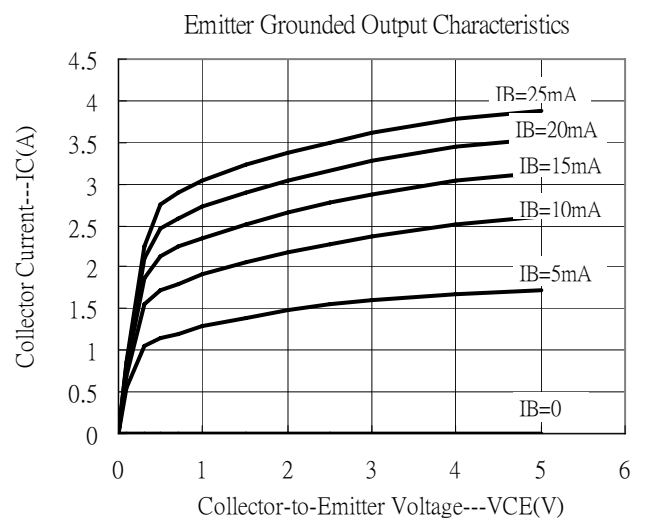
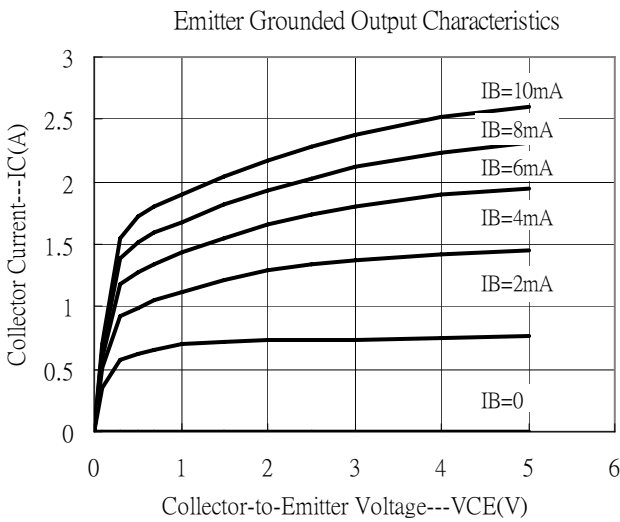
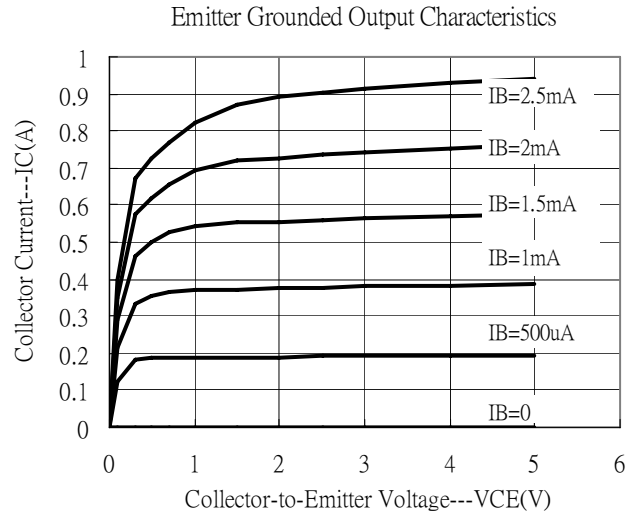
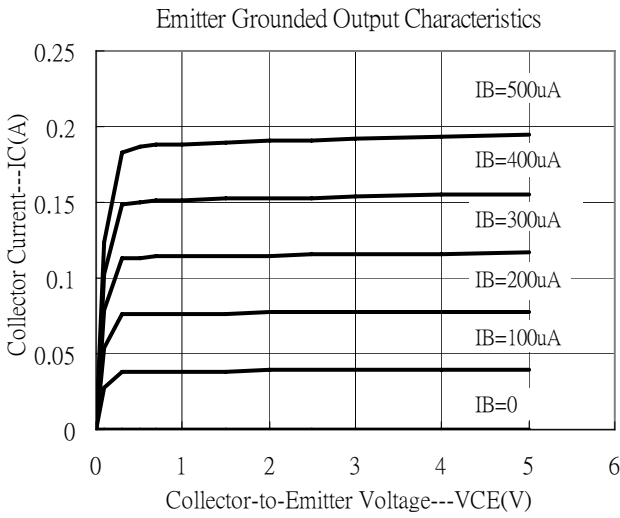
Classification Of hFE 2

Rank	P	E
Range	180~390	270~560

Ordering Information

Device	Package	Shipping	Marking
BTD882I3	TO-251 (RoHS compliant)	80 pcs / tube, 50 tubes/box, 10 boxes/carton	D882

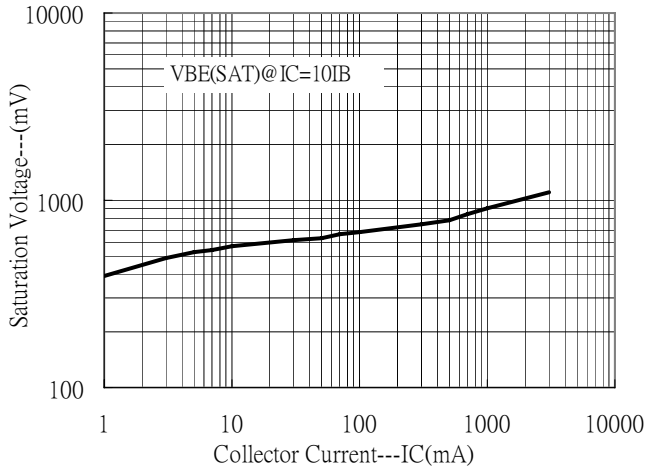
Characteristic Curves



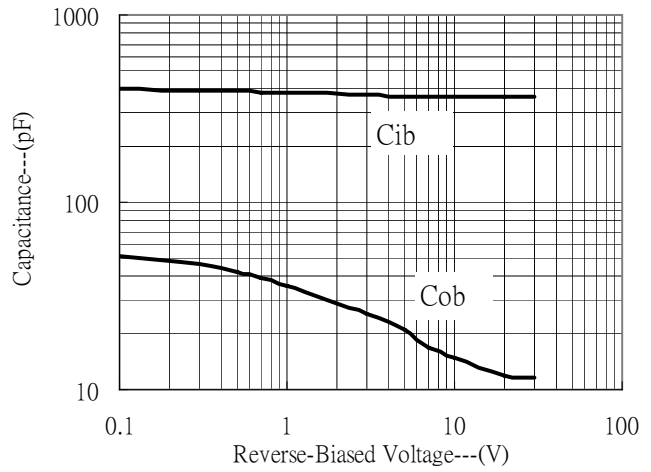


Characteristic Curves(Cont.)

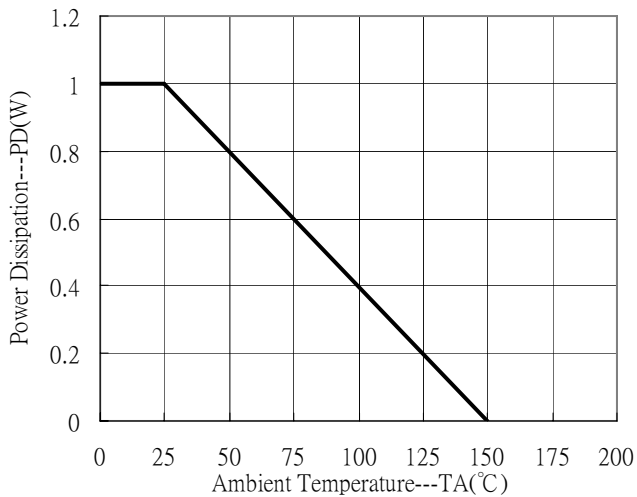
Saturation Voltage vs Collector Current



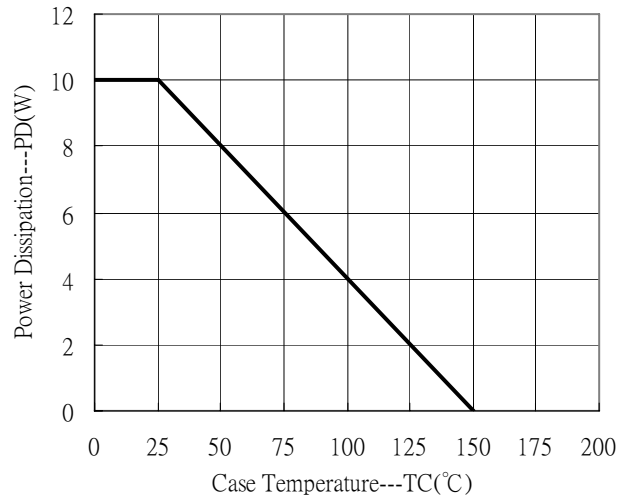
Capacitance vs Reverse-Biased Voltage



Power Derating Curve



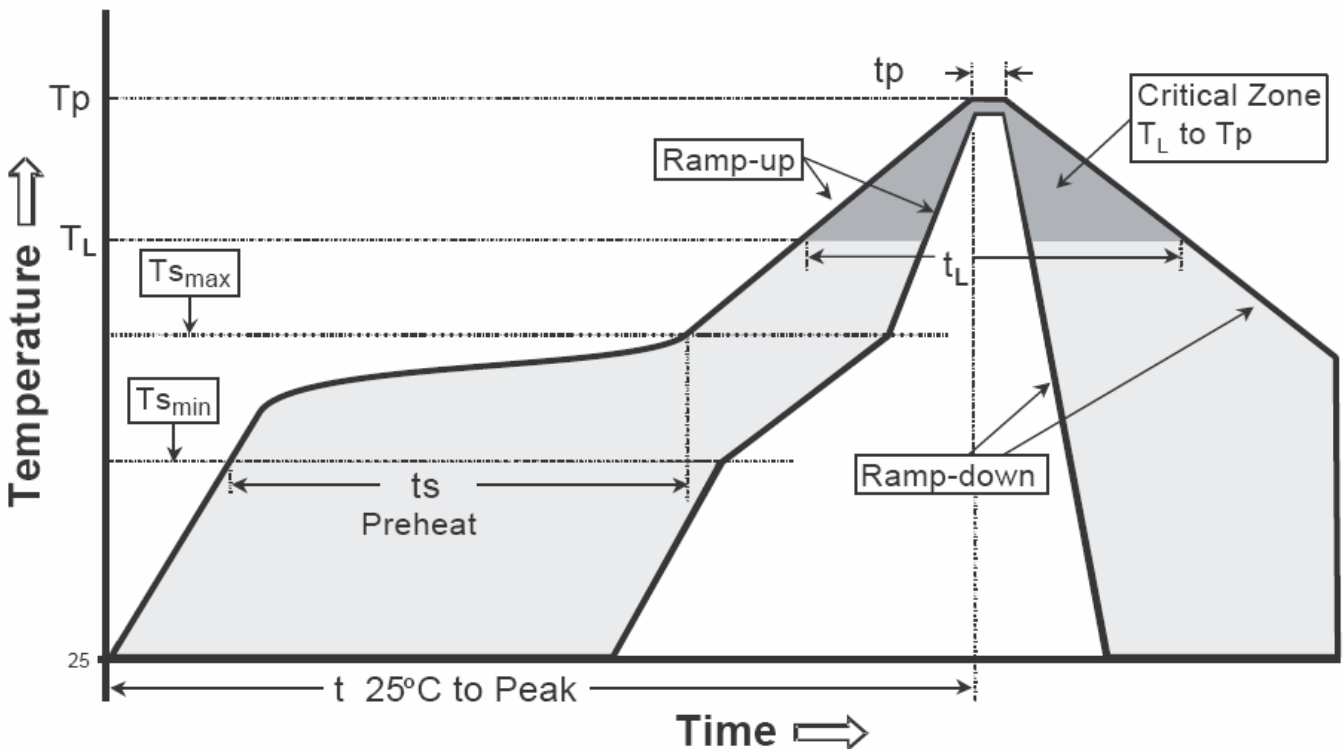
Power Derating Curve



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

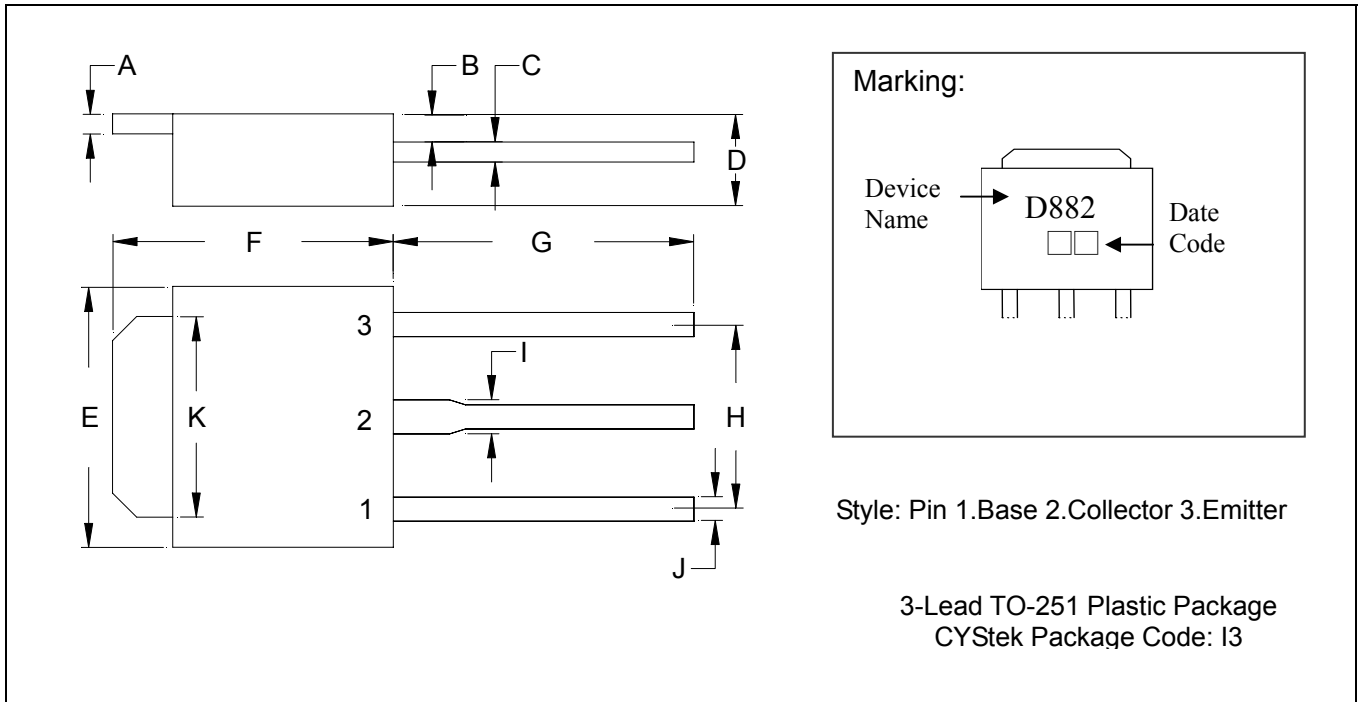
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-251 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.2559	-	6.50	-
B	0.0354	0.0591	0.90	1.50	H	-	*0.1811	-	*4.60
C	0.0177	0.0236	0.45	0.60	I	-	0.0449	-	1.14
D	0.0866	0.0945	2.20	2.40	J	-	0.0346	-	0.88
E	0.2441	0.2677	6.20	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2677	0.2835	6.80	7.20					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: KFC; pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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